



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} | I _D T _A = +25°C | | |
|----------------------|--------------------------------|--|--|--|
| | 45mΩ @ V _{GS} = 4.5V | | | |
| 12V | 64mΩ @ V _{GS} = 2.5V | 3.2A | | |
| 124 | 85mΩ @ V _{GS} = 1.8V | | | |
| | 100mΩ @ V _{GS} = 1.5V | | | |

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions
- Backlighting
- Load Switch

Fast Switching SpeedESD Protected Gate

Low On-Resistance Low Input/Output Leakage

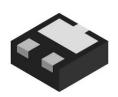
Features and Benefits

- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

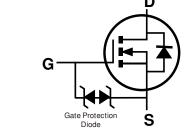
Mechanical Data

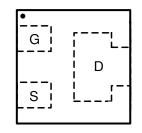
- Case: X2-DFN1010-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0015 Grams (Approximate)





X2-DFN1010-3





Bottom View

Equivalent Circuit

Pin-out Top View

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|--------------|------------------|
| DMN1045UFR4-7 | X2-DFN1010-3 | 3000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



10 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

| Year | 201 | 4 | 2015 | | 2016 | 20 | 17 | 2018 | | 2019 | 2 | 020 | |
|-------|-----|-----|------|-----|------|-----|-----|------|-----|------|-----|-----|--|
| Code | В | | С | | D | | Ξ | F | | G | | Н | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec | |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D | |



Maximum Ratings (@T_A = +25°C, unless otherwise specified)

| Characteristic | Symbol | Value | Unit |
|--|-----------------|------------|------|
| Drain-Source Voltage | V_{DSS} | 12 | V |
| Gate-Source Voltage | V_{GSS} | ±8 | V |
| Continuous Drain Current (Note 6) V _{GS} = 4.5V | I _D | 3.2 2.5 | А |
| Pulsed Drain Current (10µs pulse, Duty cycle = 1%) | I _{DM} | 15 | А |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | P_{D} | 0.5 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5) | R _{0JA} | 251 | °C/W |
| Total Power Dissipation (Note 6) | P_{D} | 1.26 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6) | $R_{\theta JA}$ | 99 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

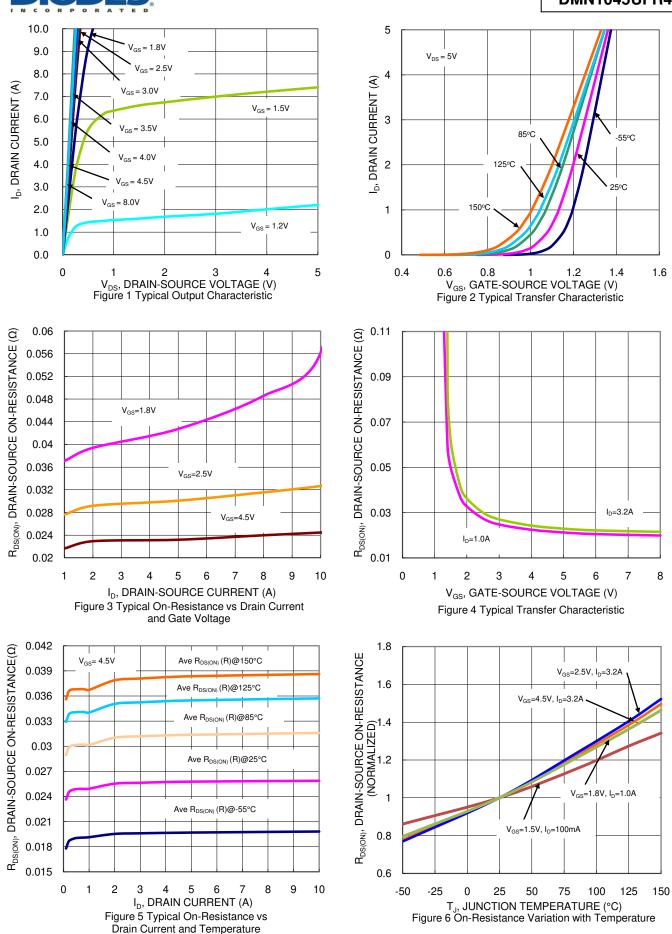
Electrical Characteristics (@TA = +25°C, unless otherwise specified)

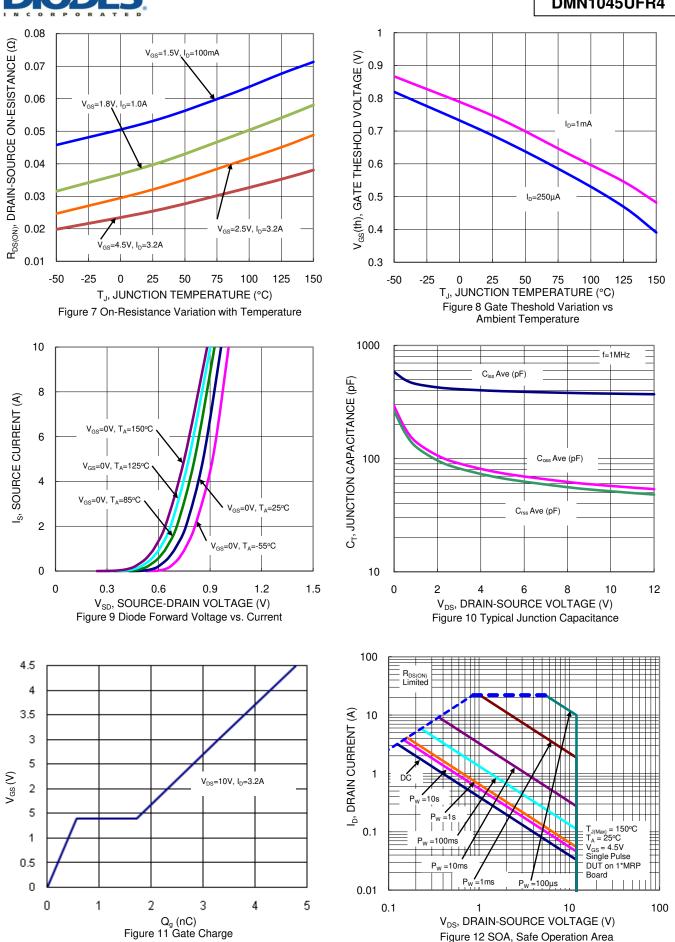
| Characteristic | Symbol | Min | Tyro | Max | Unit | Test Condition |
|-----------------------------------|---------------------|--------|------|-------|-------|---|
| OFF CHARACTERISTICS (Note 7) | Syllibol | IVIIII | Тур | IVIAX | Ullit | rest Condition |
| , , | | 4.0 | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 12 | | | V | $V_{GS} = 0V, I_D = 250 \mu A$ |
| Zero Gate Voltage Drain Current | I_{DSS} | | _ | 1 | μΑ | $V_{DS} = 12V, V_{GS} = 0V$ |
| Gate-Source Leakage | I_{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 8V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 0.4 | | 1.0 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ |
| | | | 25 | 45 | | $V_{GS} = 4.5V, I_D = 3.2A$ |
| Static Drain-Source On-Resistance | | _ | 32 | 64 | mΩ | $V_{GS} = 2.5V, I_D = 3.2A$ |
| Static Diain-Source On-nesistance | R _{DS(ON)} | | 40 | 85 | 11122 | $V_{GS} = 1.8V, I_D = 1A$ |
| | | | 50 | 100 | | $V_{GS} = 1.5V, I_D = 0.1A$ |
| Diode Forward Voltage | V_{SD} | | _ | 1.2 | V | V _{GS} = 0V, I _S = 1.0A |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C _{iss} | | 375 | | pF | |
| Output Capacitance | Coss | _ | 57 | _ | pF | $V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$ |
| Reverse Transfer Capacitance | C _{rss} | | 51 | | рF | |
| Total Gate Charge | Q_{g} | | 4.8 | | nC | V 45V V 10V |
| Gate-Source Charge | Q _{gs} | | 0.6 | | nC | $V_{GS} = 4.5V, V_{DS} = 10V$ $I_{D} = 3.2A$ |
| Gate-Drain Charge | Q_{gd} | | 1.2 | | nC | ID = 3.2A |
| Turn-On Delay Time | t _{D(on)} | | 7 | | ns | |
| Turn-On Rise Time | t _r | | 25 | | ns | $V_{DD} = 10V, V_{GEN} = 4.5V,$ |
| Turn-Off Delay Time | t _{D(off)} | | 93 | | ns | $R_{GEN} = 6\Omega$, $I_D = 3.2A$ |
| Turn-Off Fall Time | t _f | _ | 48 | _ | ns | |

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided. 7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

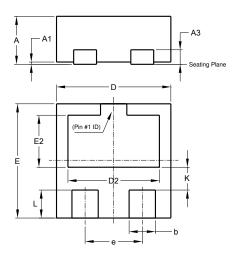






Package Outline Dimensions

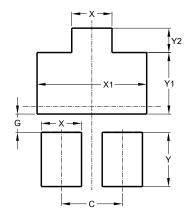
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| X2-DFN1010-3 | | | | | | | |
|----------------------|-------|-------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | - | 0.40 | 0.39 | | | | |
| A1 | 0.00 | 0.05 | 0.02 | | | | |
| A 3 | - | 1 | 0.13 | | | | |
| b | 0.18 | 0.28 | 0.23 | | | | |
| D | 0.95 | 1.05 | 1.00 | | | | |
| D2 | 0.70 | 0.90 | 0.80 | | | | |
| E | 0.95 | 1.05 | 1.00 | | | | |
| E2 | 0.36 | 0.56 | 0.46 | | | | |
| е | - | - | 0.50 | | | | |
| K | - | 1 | 0.20 | | | | |
| Ĺ | 0.195 | 0.295 | 0.245 | | | | |
| All Dimensions in mm | | | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| X2-DFN1010-3 | | | | |
|----------------------|-------|--|--|--|
| Dimensions | Value | | | |
| С | 0.500 | | | |
| G | 0.150 | | | |
| Х | 0.330 | | | |
| X1 | 0.900 | | | |
| Υ | 0.445 | | | |
| Y1 | 0.505 | | | |
| Y2 | 0.200 | | | |
| All Dimensions in mm | | | | |



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